






	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI2316BDS-T1-GE3</a></p>
	<p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p>
	<p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 4.5A SOT23-3</p>
	<p><b>Datenblätter:</b>  <a href="#">SI2316BDS-T1-GE3.pdf</a></p>
	<p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p>
	<p><b>Lagerzustand:</b> New original, 58412 pcs Stock Available.</p>
	<p><b>Liefern von:</b> Hong Kong</p>
<p>Image may be representation. See specs for product details.</p>	<p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>

### Spezifikationen

Teilenummer	<a href="#">SI2316BDS-T1-GE3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET N-CH 30V 4.5A SOT23-3
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	58412 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.25W (Ta), 1.66W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.5A (Tc)
Rds On (Max) @ Id, Vgs	50 mOhm @ 3.9A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	9.6nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	350pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Original-Reel®

















SI2316BDS-T1-GE3 ist neu im Original, Suche SI2316BDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2316BDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2316BDS-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI2316DS-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 2.9A SOT23-3</p>	 <p><b>SI2316BDS-T1-E3</b> Vishay / Siliconix MOSFET N-CH 30V 4.5A SOT-23</p>	 <p><b>SI2316BDS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.5A SOT23-3</p>	 <p><b>SI2316-DS</b> VISHAY SI2316-DS VISHAY</p>
 <p><b>SI2316DS</b> 89K SI2316DS 89K</p>	 <p><b>SI2316BDS-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 4.5A SOT-23</p>	 <p><b>SI2316DS-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 2.9A SOT23-3</p>	 <p><b>SI2316DS-T1-E3</b> Vishay / Siliconix MOSFET N-CH 30V 2.9A SOT23-3</p>

### heiße Teile

Mehr

 SI2312DS-T1-GE3	 SI2313DS	 SI2313DS-T1-E3	 SI2313DS-T1-GE3	 SI2314DS
 SI2314DS-T1-E3	 SI2314DS-T1-GE3	 SI2314EDS	 SI2314EDS-T1-E3	 SI2314EDS-T1-E3
 SI2314EDS-T1-GE3	 SI2314EDS-T1-GE3	 SI2315BDS	 SI2315BDS-T1-E3	 SI2315BDS-T1-E3
 SI2315BDS-T1-GE3	 SI2315BDS-T1-GE3	 SI2315DS	 SI2315DS-T1	 SI2315DS-T1-E3
 SI2315DS-T1-GE3	 SI2316-DS	 SI2316BDS-T1-E3	 SI2316BDS-T1-E3	 SI2316BDS-T1-GE3
 SI2316DS	 SI2316DS-T1-E3	 SI2316DS-T1-E3	 SI2316DS-T1-GE3	 SI2316DS-T1-GE3
 SI2317DS	 SI2317DS-T1-E3	 SI2318ADS-T1-GE3	 SI2318BDS-T1-E3	 SI2318BDS-T1-GE3
 SI2318CDS-T1-E3	 SI2318CDS-T1-GE3	 SI2318CDS-T1-GE3	 SI2318DS	 SI2318DS-T1-E3
 SI2318DS-T1-E3	 SI2318DS-T1-GE3	 SI2318DS-T1-GE3	 SI2319ADS-T1-GE3	 SI2319C95TF
 SI2319CDS-T1-E3	 SI2319CDS-T1-GE3	 SI2319CDS-T1-GE3	 SI2319DDS-T1-GE3	 SI2319DS

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited